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# N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ ) TYP.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)			
80	2 at V <sub>GS</sub> = 10 V	150	119 nC			

### **FEATURES**

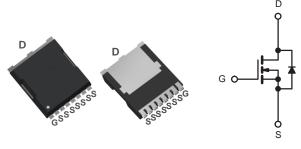
- DT-Trench Power MOSFET
- $\bullet$  100 %  $R_g$  and UIS tested



### **APPLICATIONS**

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management





N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (7)	$\Gamma_{\rm C}$ = 25 °C, unless othe	rwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	80	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	7 v		
Continuous Drain Current (T. 150 °C)	T <sub>C</sub> = 25 °C		150		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 100 °C	I <sub>D</sub>	133	T ,	
Pulsed Drain Current (t = 100 μs)	I <sub>DM</sub>	600	A		
Avalanche Current L = 0.1 mH		I <sub>AS</sub>	145		
Single Avalanche Energy <sup>a</sup>	L = U.1 IIIII	E <sub>AS</sub>	1010	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	216	w	
iviaximum rower bissipation 4	T <sub>C</sub> = 100 °C	P <sub>D</sub>	84.6 b	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS								
PARAMETER	SYMBOL	LIMIT	UNIT					
Junction-to-Ambient (PCB Mount) <sup>c</sup>	t ≤ 10 s	R <sub>thJA</sub>	20	°C/W				
Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	0.5	- C/VV				

#### Notes

- a. Duty cycle  $\leq 1 \%$ .
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Static								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_D=250\;\mu A$	1.5	-	3.5	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V$ , $V_{GS} = \pm 20 V$	-	-	± 100	nA		
		V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 64$ V, $V_{GS} = 0$ V, $T_J = 85\ ^{\circ}C$	-	-	10	μA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	150	-	-	Α		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	2	2.6	mΩ		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A	-	166	-	S		
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		-	9878	-	pF		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 40 \text{ V}, f = 1 \text{ MHz}$	-	3294	-			
Reverse Transfer Capacitance	C <sub>rss</sub>		-	76	-			
Total Gate Charge <sup>c</sup>	$Q_g$		-	119	-			
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		42	-	nC		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	33	-			
Gate Resistance	$R_g$	f = 1 MHz	-	2.0	-	Ω		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	30	-			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}=40~V,~I_D=20~A,~R_g=6\Omega$	-	48	-	ns		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}$	-	59	-			
Fall Time <sup>c</sup>	t <sub>f</sub>		-	33	-			
Drain-Source Body Diode Ratings and	Characterist	ics <sup>b</sup> (T <sub>C</sub> = 25 °C)	•					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	150	Α		
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	600	Α		
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	-	1	V		
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs	-	105	-	ns		
Reverse Recovery Charge	$Q_{rr}$	i <sub>F</sub> = 20 A, αί/αι = 100 A/μs	-	289	-	nC		

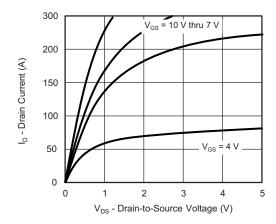
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

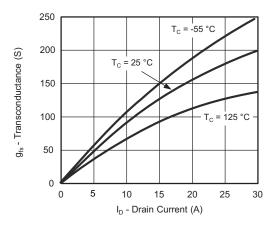
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



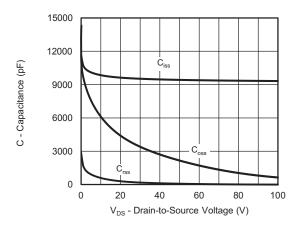
## **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



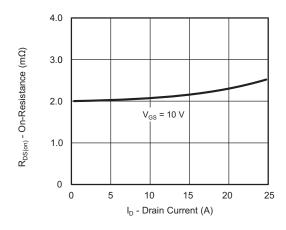
#### **Output Characteristics**



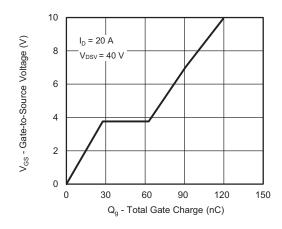
Transconductance



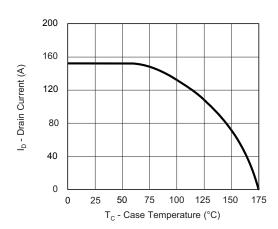
Capacitance



**On-Resistance vs. Drain Current** 



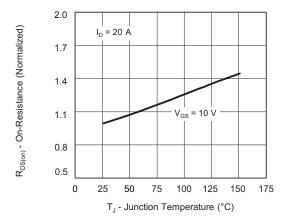
Gate Charge



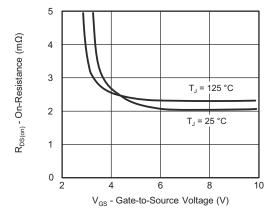
**Current De-Rating** 



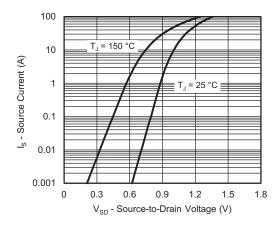
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



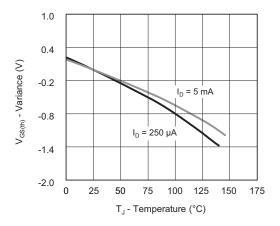
On-Resistance vs. Junction Temperature



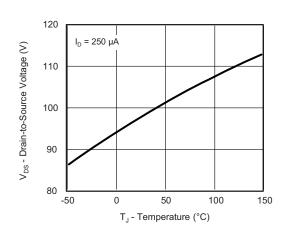
On-Resistance vs. Gate-to-Source Voltage



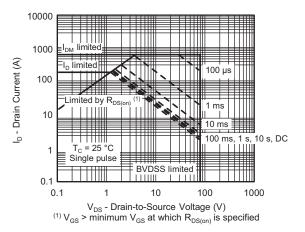
Source Drain Diode Forward Voltage



**Threshold Voltage** 



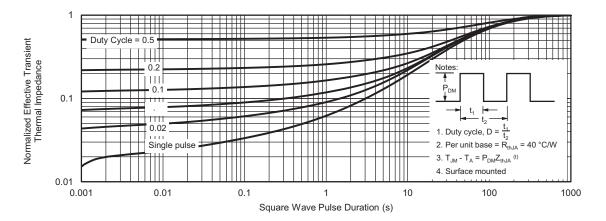
Drain Source Breakdown vs. Junction Temperature



Safe Operating Area



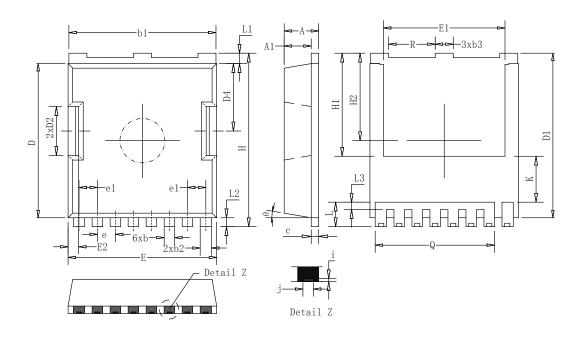
## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



# **TOLL PACKAGE OUTLINE**



# COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
A	2.05	2.30	2.65	E2	0.40	0.70	0.90
A1	1.50	1.80	2.10	Н	11.30	11.70	12.10
b	0.50	0.70	0.90	H1	6.95 BSC		
b1	9.50	9.80	10.05	H2	5.90 BSC		
b2	0.50	0.75	1.00	i	0.10 REF		
b3	1.00	1.20	1.45	j	0.35 REF		
c	0.30	0.50	0.75	K	3.10 REF		
D	10.10	10.40	10.70	L	1.45 1.65 1.85		1.85
D1	10.80	11.10	11.40	L1	0.50	0.70	0.90
D2	3.10	3.30	3.50	L2	0.40	0.60	0.80
D4	4.35	4.55	4.80	L3	0.30	0.50	0.70
e	1.20 BSC			Q	7.95 REF		
e1	1.225 BSC			R	2.80	3.10	3.35
Е	9.65	9.90	10.15	θ	10°REF		
E1	7.80	8.10	8.50				





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